Analog Multiplexers/ Demultiplexers with Injection Current Effect Control with LSTTL Compatible Inputs

Automotive Customized

MC74HCT4851A, MC74HCT4852A

This device is pin compatible to standard HC405x and MC1405xB analog mux/demux devices, but feature injection current effect control. This makes them especially suited for usage in automotive applications where voltages in excess of normal logic voltage are common.

The injection current effect control allows signals at disabled analog input channels to exceed the supply voltage range without affecting the signal of the enabled analog channel. This eliminates the need for external diode/ resistor networks typically used to keep the analog channel signals within the supply voltage range.

The devices utilize low power silicon gate CMOS technology. The Channel Select and Enable inputs are compatible with standard CMOS or LSTTL outputs.

Features

- Injection Current Cross-Coupling Less than 1mV/mA (See Figure 6)
- Pin Compatible to HC405x and MC1405xB Devices
- Power Supply Range (V_{CC} GND) = 4.5 to 5.5 V
- In Compliance With the Requirements of JEDEC Standard No. 7 A
- Chip Complexity: 154 FETs or 36 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B





SOIC-16 WIDE DW SUFFIX CASE 751G





TSSOP-16 DT SUFFIX CASE 948F



X = 1 or 2

= Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

1

X0 13 X1 X2¹⁵ ANALOG INPUTS/ OUTPUTS MULTIPLEXER/ Х3-COMMON **DEMULTIPLEXER** OUTPUT/ **INPUT** X5 Х6-11 CHANNEL 10 SELECT INPUTS C 6 **ENABLE** PIN 16 = V_{CC} PIN 8 = GND

Figure 1. MC74HCT4851A Logic Diagram Single-Pole, 8-Position Plus Common Off

FUNCTION TABLE - MC74HCT4851A

Conti	rol Inp			
	;	Selec	t	
Enable	С	В	Α	ON Channels
L	L	L	L	X0
L	L	L	Н	X1
L	L	Н	L	X2
L	L	Н	Н	X3
L	H	L	L	X4
L	Н	L	Н	X5
L	Н	Н	L	X6
L	Н	Н	Н	X7
Н	X	Χ	Χ	NONE

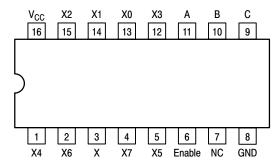


Figure 2. MC74HCT4851A 16-Lead Pinout (Top View)

X1 13 X2 15 X SWITCH хз-ANALOG INPUTS/OUTPUTS COMMON **OUTPUTS/INPUTS** Υ1 Y SWITCH 10 CHANNEL-SELECT PIN 16 = V_{CC} PIN 8 = GND INPUTS В ENABLE 6

Figure 3. MC74HCT4852A Logic Diagram Double-Pole, 4-Position Plus Common Off

FUNCTION TABLE - MC74HCT4852A

Contr	ol Input				
	Se				
Enable	В	Α	ON Ch	annels	
L	L	L	Y0	X0	
L	L	Н	Y1	X1	
L	Н	L	Y2	X2	
L	Н	Н	Y3	X3	
Н	Х	X	NONE		

X = Don't Care

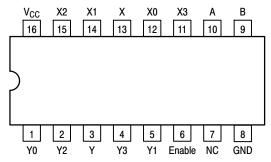


Figure 4. MC74HCT4852A 16-Lead Pinout (Top View)

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V
V _{in}	DC Input Voltage (Any Pin) (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
I	DC Current, Into or Out of Any Pin	±25	mA
P _D	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature Range	-65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds SOIC or TSSOP Package	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage (Refer	4.5	5.5	V	
V _{in}	DC Input Voltage (Any Pin) (Refer	GND	V _{CC}	V	
V _{IO} *	Static or Dynamic Voltage Across Swi	0.0	1.2	V	
T _A	Operating Temperature Range, All Pa	ckage Types	– 55	+ 125	°C
t _r , t _f	Input Rise/Fall Time (Channel Select or Enable Inputs)	0 0 0	1000 500 400	ns	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC CHARACTERISTICS — Digital Section (Voltages Referenced to GND) V_{EE} = GND, Except Where Noted

			v _{cc}	Guara	Guaranteed Limit		
Symbol	Parameter	Condition	v	-55 to 25°C	≤ 85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec	4.5 to 5.5	2.0	2.0	2.0	V
V _{IL}	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs	R _{on} = Per Spec	4.5 to 5.5	0.8	8.0	0.8	٧
I _{in}	Maximum Input Leakage Current on Digital Pins (Enable/A/B/C)	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in(digital)} = V_{CC}$ or GND $V_{in(analog)} = GND$	5.5	2.0	20	40	μΑ

^{*}For voltage drops across switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC CHARACTERISTICS — Analog Section

				Guaranteed Limit			
Symbol	Parameter	Condition	V _{CC}	-55 to 25°C	≤ 85 °C	≤125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{\text{in}} = V_{\text{IL}} \text{ or } V_{\text{IH}}; V_{\text{IS}} = V_{\text{CC}} \text{ to}$ GND (Note 1); $I_{\text{S}} \leq 2.0 \text{ mA}$ (Note 2)	4.5 5.5	550 400	650 500	750 600	Ω
ΔR_{on}	Delta "ON" Resistance	$\begin{aligned} &V_{in} = V_{IL} \text{ or } V_{IH}; \ V_{IS} = V_{CC}/2\\ &\text{(Note 1); } I_S \leq 2.0 \text{ mA (Note 2)} \end{aligned}$	4.5 5.5	80 60	100 80	120 100	Ω
l _{off}	Maximum Off-Channel Leakage Current, Any One Channel Common Channel	V _{in} = V _{CC} or GND	5.5	±0.1 ±0.1	±0.1 ±0.1	±0.1 ±0.1	μΑ
I _{on}	Maximum On-Channel Leakage Channel-to-Channel	V _{in} = V _{CC} or GND	5.5	±0.1	±0.1	±0.1	μΑ

AC CHARACTERISTICS (CL = 50 pF, Input t_r = t_f = 6 ns, V_{CC} = 5.0 V \pm 10%)

Symbol	Parameter	V _{CC}	-55 to 25°C	≤ 85°C	≤125°C	Unit
t _{PHL} , t _{PLH}	Maximum Propagation Delay, Analog Input to Analog Output	5.0	40	45	50	ns
t _{PHL} , t _{PHZ,PZH} t _{PLH} , t _{PLZ,PZL}	Maximum Propagation Delay, Enable or Channel-Select to Analog Output	5.0	80	90	100	ns
C _{in}	Maximum Input Capacitance Digital Pins (All Switches Off) Any Single Analog Pin (All Switches Off) Common Analog Pin		10 35 40	10 35 40	10 35 40	pF
C _{PD}	Power Dissipation Capacitance Typical	5.0	20			pF

INJECTION CURRENT COUPLING SPECIFICATIONS (V $_{CC}$ = 5V, T_A = $-55^{\circ}C$ to $+125^{\circ}C$)

Symbol	Parameter	Condition	Тур	Max	Unit
VΔ _{out}	Maximum Shift of Output Voltage of Enabled Analog Channel	$\begin{split} &I_{in}{}^{\star} \leq 1 \text{ mA, } R_S \leq 3,9 \text{ k}\Omega \\ &I_{in}{}^{\star} \leq 10 \text{ mA, } R_S \leq 3,9 \text{ k}\Omega \\ &I_{in}{}^{\star} \leq 1 \text{ mA, } R_S \leq 20 \text{ k}\Omega \\ &I_{in}{}^{\star} \leq 10 \text{ mA, } R_S \leq 20 \text{ k}\Omega \end{split}$	0.1 1.0 0.5 5.0	1.0 5.0 2.0 20	mV

^{*} I_{in} = Total current injected into all disabled channels.

V_{IS} is the input voltage of an analog I/O pin.
 I_S is the currebnt flowing in or out of analog I/O pin.

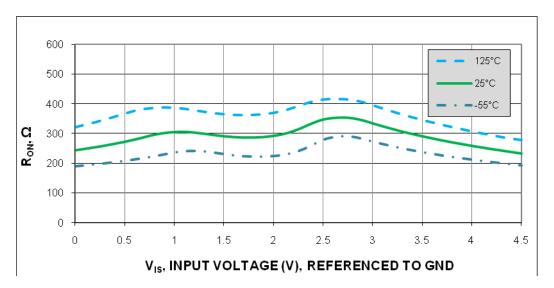


Figure 5. Typical On Resistance V_{CC} = 4.5V

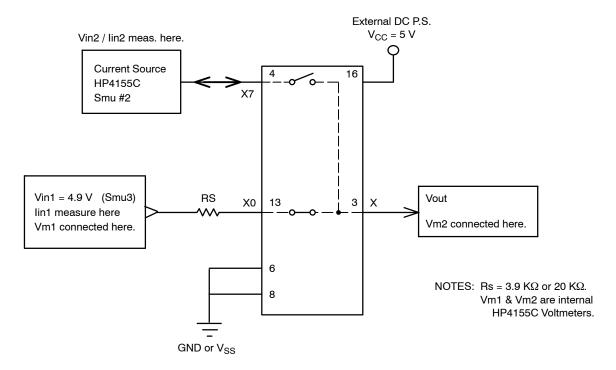


Figure 6. Injection Current Coupling Specification

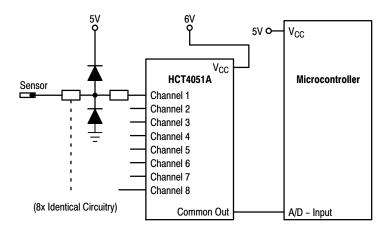


Figure 7. Actual Technology

Requires 32 passive components and one extra 6V regulator to suppress injection current into a standard HCT4051 multiplexer

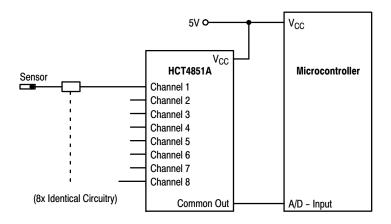


Figure 8. MC74HCT4851A Solution
Solution by applying the HCT4851A multiplexer

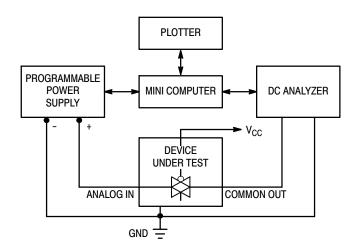


Figure 9. On Resistance Test Set-Up

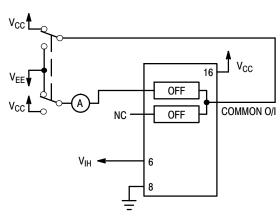


Figure 10. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

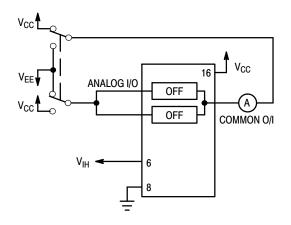


Figure 11. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

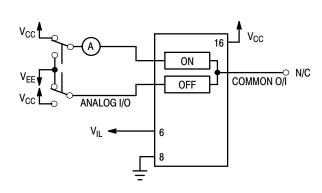


Figure 12. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

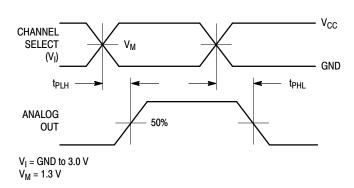
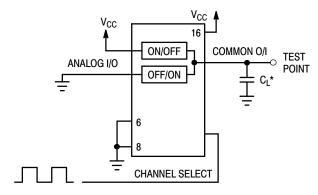


Figure 13. Propagation Delays, Channel Select to Analog Out



*Includes all probe and jig capacitance

Figure 14. Propagation Delay, Test Set-Up Channel Select to Analog Out

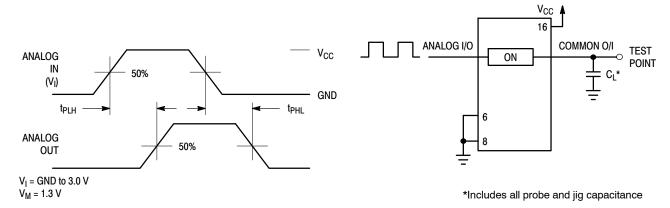


Figure 15. Propagation Delays, Analog In to Analog Out

Figure 16. Propagation Delay, Test Set-Up
Analog In to Analog Out

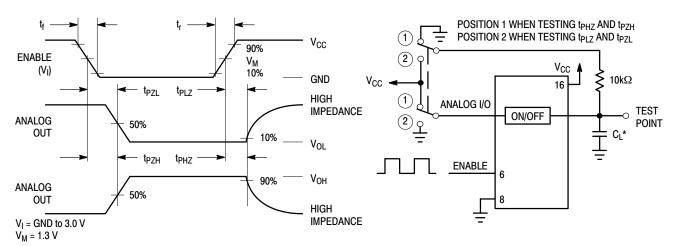


Figure 17. Propagation Delays, Enable to Analog Out

Figure 18. Propagation Delay, Test Set-Up Enable to Analog Out

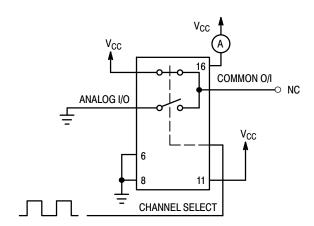


Figure 19. Power Dissipation Capacitance, Test Set-Up

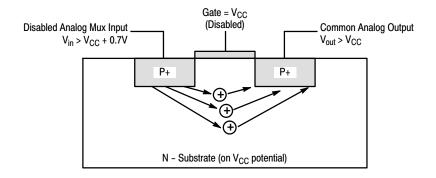


Figure 20. Diagram of Bipolar Coupling Mechanism

Appears if V_{in} exceeds $V_{\text{CC}}\text{,}$ driving injection current into the substrate

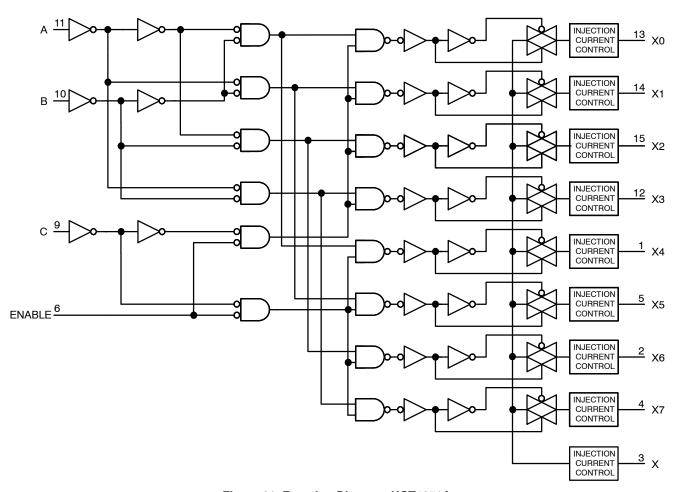


Figure 21. Function Diagram, HCT4851A

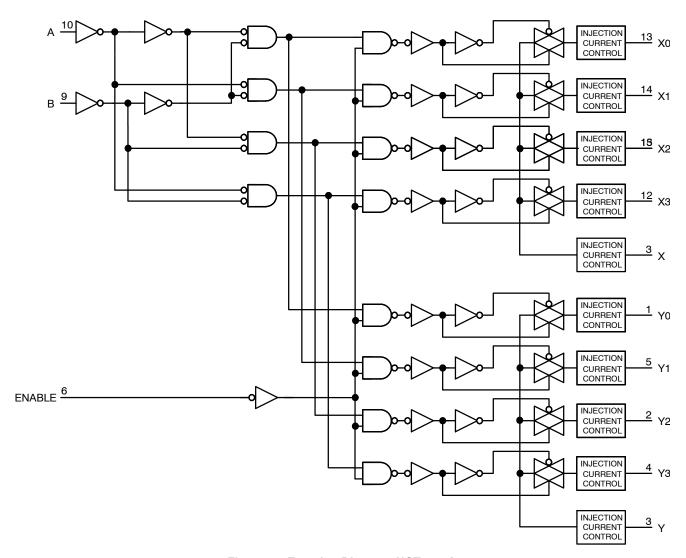


Figure 22. Function Diagram, HCT4852A

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT4851ADG	SOIC-16	48 Units / Rail
MC74HCT4851ADR2G	(Pb-Free)	2500 Units / Tape & Reel
NLV74HCT4851ADRG*		2500 Units / Tape & Reel
MC74HCT4851AADR2G		2500 Units / Tape & Reel
MC74HCT4851ADTG	TSSOP-16	48 Units / Rail
M74HCT4851ADTR2G	(Pb-Free)	2500 Units / Tape & Reel
NLVHCT4851ADTR2G*		2500 Units / Tape & Reel
M74HCT4851ADWR2G	SOIC-16 WIDE (Pb-Free)	1000 Units / Tape & Reel
MC74HCT4852ADG	SOIC-16	48 Units / Rail
MC74HCT4852ADR2G	(Pb-Free)	2500 Units / Tape & Reel
MC74HCT4852ADTG	TSSOP-16	48 Units / Rail
M74HCT4852ADTR2G	(Pb-Free)	2500 Units / Tape & Reel
NLVHCT4852ADTR2G*	7	2500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE



DATE 29 DEC 2006

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION		BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.		7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	OOL DEDING	COOTDONT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		i.40 — →
								- 0	.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				10% 1.12
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	Τ\		1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			, L .	'0
3. 4.	DRAIN, #2	3. 4.	CATHODE	3. 4.	GATE P-CH	1)		- —	
4. 5.	DRAIN, #2	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\		, , , , , , , , , , , , , , , , , , , 	
5. 6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16	5X 1 -	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.5	58	, L
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	•,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.		13.	GATE N-CH	.,			
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPU	T)			V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				1 <u>+=</u> 1- 1
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	.,			
								□ 8	9 + - + -
									~
									' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '
									DIMENSIONS: MILLIMETERS

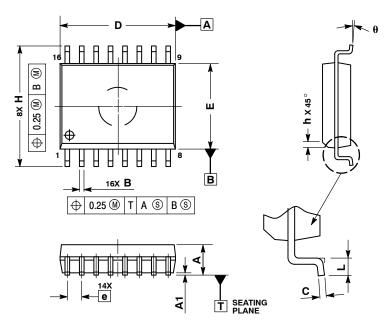
DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
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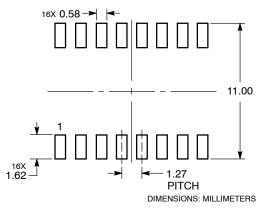


SOIC-16 WB CASE 751G-03 ISSUE D

DATE 12 FEB 2013



SOLDERING FOOTPRINT

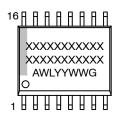


NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INLCUDE MOLD PROTRUSION.
- MOLID PROTRUSION.
 MAXIMUM MOLID PROTRUSION 0.15 PER SIDE.
 DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	10.15	10.45	
Е	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
q	0 °	7 °	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location Α

WL = Wafer Lot YY = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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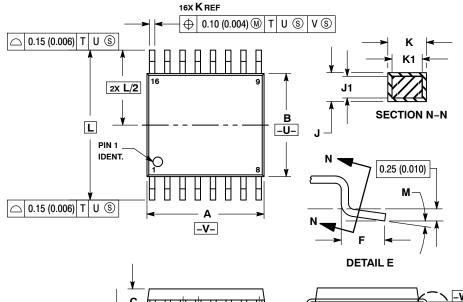
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006



NOTES

- JIES:
 DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD
 FLASH. PROTRUSIONS OR GATE BURRS.
 MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8°	0 °	8°

SOLDERING FOOTPRINT

G



GENERIC MARKING DIAGRAM*

168888888 XXXX XXXX **ALYW** 188888888

XXXX = Specific Device Code Α = Assembly Location = Wafer Lot L

Υ = Year W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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